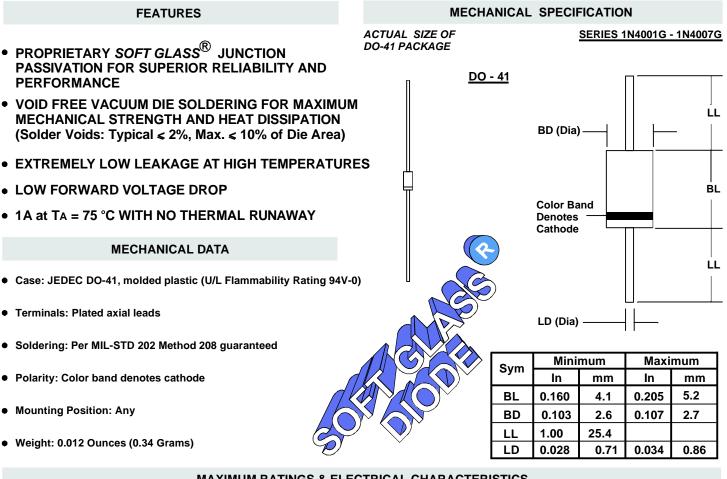


## **1 AMP SOFT GLASS PASSIVATED SILICON DIODES**



## **MAXIMUM RATINGS & ELECTRICAL CHARACTERISTICS**

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive loads, derate current by 20%.

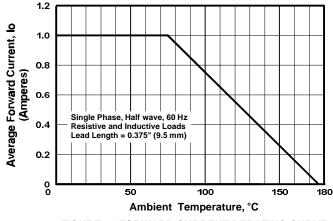
PARAMETER (TEST CONDITIONS)	SYMBOL	RATINGS							UNITS
Series Number		1N 4001G	1N 4002G	1N 4003G	1N 4004G	1N 4005G	1N 4006G	1N 4007G	
Maximum DC Blocking Voltage	Vrm	50	100	200	400	600	800	1000	VOLTS
Maximum RMS Voltage	Vrms	35	70	140	280	420	560	700	
Maximum Peak Recurrent Reverse Voltage	Vrrm	50	100	200	400	600	800	1000	
Average Forward Rectified Current @ TA = 75 °C (Lead length = 0.375 in. (9.5 mm))	lo	1						AMPS	
Peak Forward Surge Current ( 8.3 mSec single half sine wave superimposed on rated load)	IFSM	50							
Maximum Forward Voltage at 1 Amp DC	Vfm	1							VOLTS
Maximum Full Cycle Reverse Current @ T∟ = 75 °C (Note 1)	IRM(AV)	10							μΑ
Maximum Average DC Reverse Current@ TA = 25°CAt Rated DC Blocking Voltage@ TA = 100°C	Iгм	1 20							
Typical Thermal Resistance, Junction to Ambient (Note 1)	Reja	30							°C/W
Typical Junction Capacitance (Note 2)	CJ	10							pF
Operating and Storage Temperature Range	TJ, TSTG	-65 to +175							°C

NOTES: (1) Lead length = 0.375 in. (9.5 mm)

(2) Measured at 1MHz & applied reverse voltage of 4 volts



## **1 AMP SOFT GLASS PASSIVATED SILICON DIODES**



## **RATING & CHARACTERISTIC CURVES FOR SERIES 1N4001G - 1N4007G**

FIGURE 1. FORWARD CURRENT DERATING CURVE

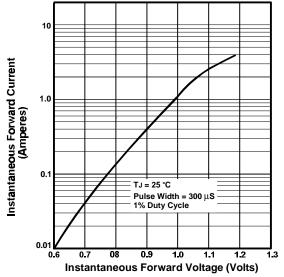


FIGURE 3. TYPICAL FORWARD CHARACTERISTIC PER DIODE

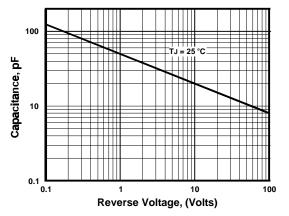


FIGURE 5. TYPICAL JUNCTION CAPACITANCE PER DIODE

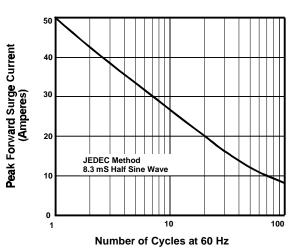
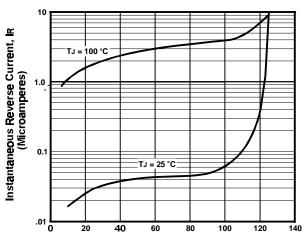


FIGURE 2. MAXIMUM NON-REPETITIVE SURGE CURRENT



Percent of Rated Peak Reverse Voltage FIGURE 4. TYPICAL REVERSE CHARACTERISTICS

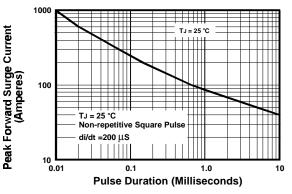


FIGURE 6. PEAK FORWARD SURGE CURRENT